

# VLSI Circuits and Design Ratioed and Pass-Transistor Logic

## Introduction

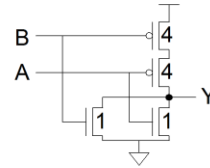
### □ What makes a circuit fast?

- $I = CdV/dt$ 
  - $dt = CdV/I$
  - $\Delta t \propto (C/I)\Delta V$
- fast circuit needs
  - low capacitance
  - high current
  - small swing

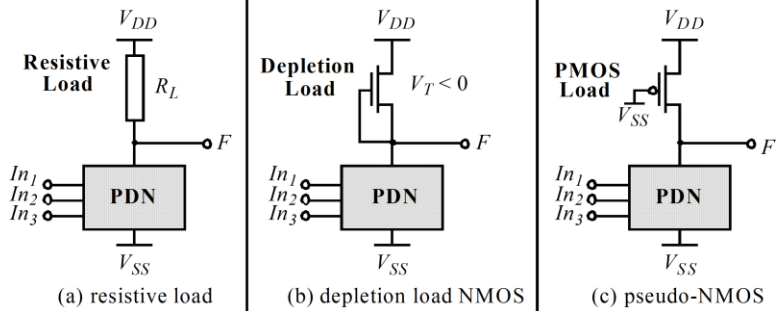
### □ PMOS are the enemy!

- high capacitance for a given current

### □ Can we take the PMOS capacitance off the input?



## Ratioed Logic



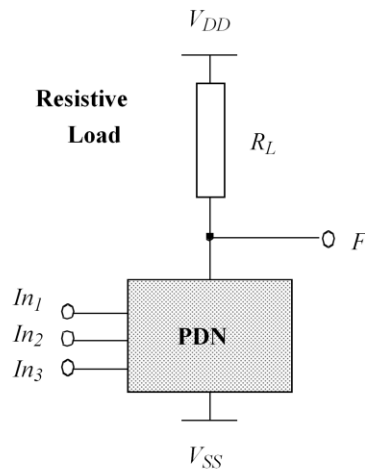
**Goal: to reduce the number of devices over complementary CMOS**

Ratioed, Pass Transistor Logic.3

The main concept of ratioed logic

- 1) Instead of using PUN and PDN (2N transistors), use **a simple load device** and PDN only.
- 2) The load device can be a passive or an active device.

## Ratioed Logic



- N transistors + Load
- $V_{OH} = V_{DD}$
- $V_{OL} = \frac{R_{PDN}}{R_{PDN} + R_L} V_{DD}$
- Asymmetrical response ( $t_r > t_f$ )
- Static power consumption
- $t_{pLH} = 0.69R_L C_L$

Ratioed, Pass Transistor Logic.4

### The over-simplified concept

- when the PDN is off,  $V_{OH}$  is pulled high by the load to strong logic '1'
- when the PDN is on, the  $V_{OL}$  will be determined by the voltage division
- $V_{OL} = (R_{PDN} / (R_{PDN} + R_L)) V_{DD}$

To keep the  $N_{ML}$  high,  $R_L \gg R_{PDN}$ . This is why it is called ratioed. The transistor must be carefully sized.

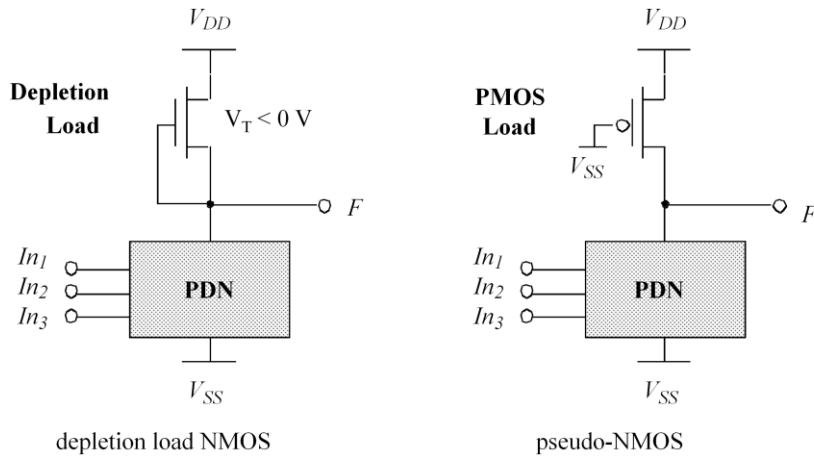
On the contrary,  $R_L$  must be small enough to allow fast switching

- 1)  $t_{pLH} = 0.69R_L C_L$
- 2)  $t_{pHL} = 0.69(R_L || R_{PN}) C_L$

$t_{pLH}$  is the main concern.  $R_L \gg R_{PDN}$  to maintain high noise margin, but small enough to enable fast switching.

Note also when the PDN is on, leakage current flows from  $V_{DD}$  to  $V_{SS}$  even in steady state.

## Active Loads



Ratioed, Pass Transistor Logic.5

The left diagram shows the usage of depletion load NMOS as load device. Yes, all transistors are NMOS. Depletion mode NMOS has  $V_T < 0$  V. This method was used during the NMOS era. The depletion NMOS is ON when  $V_{GS} = 0$  V. In this case, the depletion load transistor is always on.

The second figure shows the pseudo-NMOS inverter. It resembles depletion load, but gives superior characteristics. Unlike the depletion transistor, the PMOS transistor does not have body effect since its source is always at  $V_{DD}$ , hence its  $V_{SB}$  is constant at 0 V.

The PMOS is driven by  $V_{GSP} = -V_{DD}$  resulting in higher load current, compared to the other circuit, hence better rise time.

For pseudo-NMOS inverter, assuming  $V_{OL}$  is quite close to  $V_{SS}$  when  $V_{in} = V_{DD}$ , we make assumption that NMOS is linear and PMOS is velocity saturated. Equate currents

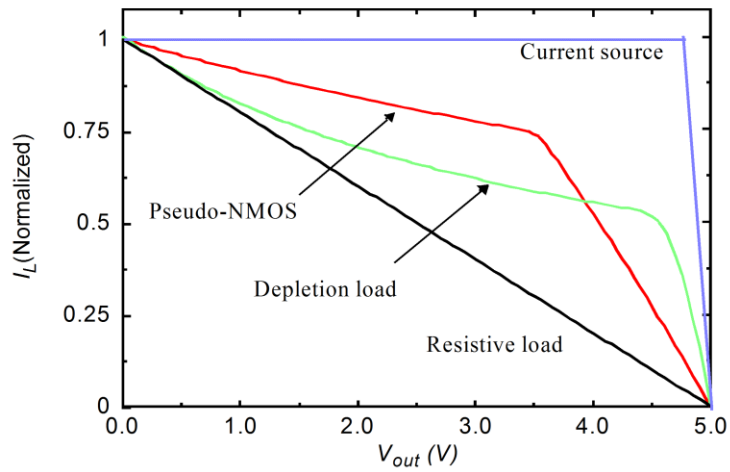
$$k_n \left( (V_{DD} - V_{Tn})V_{OL} - \frac{V_{OL}^2}{2} \right) = |k_p| \left( (V_{DD} - |V_{Tp}|) |V_{DSATp}| - \frac{V_{DSATp}^2}{2} \right)$$

Assuming  $V_{DD} - V_{Tn} \gg V_{OL}$ ,  $V_{DD} - |V_{Tp}| \gg V_{DSATp}$ , and  $V_{Tn} = |V_{Tp}|$

$$V_{OL} \approx \frac{|k_p|}{k_n} |V_{DSATp}|$$

## Load Lines of Ratioed Gates

From Rabaey 1<sup>st</sup> ed.

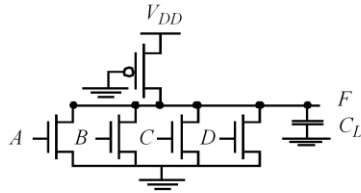


Ratioed, Pass Transistor Logic.6

When using resistive load,  $I_L = (V_{DD} - V_{OUT})/R_I$ . The current drops as the output rises.

## Pseudo-NMOS NOR Gate

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$V_{OH} = V_{DD}$  (similar to complementary CMOS)

**SMALLER AREA & LOAD BUT STATIC POWER DISSIPATION!**

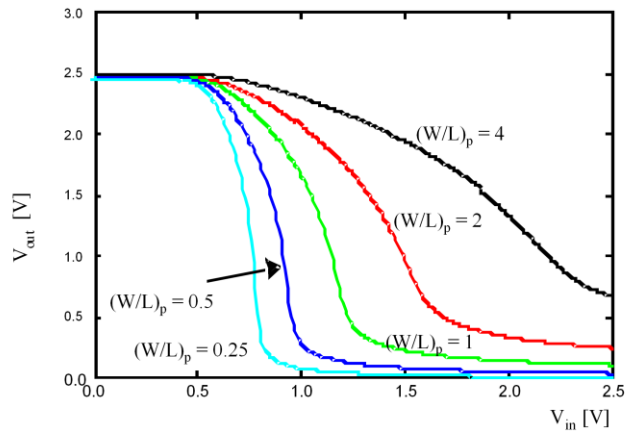
Ratioed, Pass Transistor Logic.7

Compared to complimentary CMOS,  $V_{OL} \neq 0$  V due to ratioed nature of pseudo-NMOS structure.

All ratioed logic have these common attributes

- 1) the VTC is asymmetrical
- 2) consumption of static power when output is low, due to direct current path between  $V_{DD}$  and  $V_{SS}$  through the load device
- 3) transistor scaling is very crucial
- 4) it uses only  $N+1$  transistors instead of  $2N$  for complimentary CMOS

## Pseudo-NMOS VTC



Ratioed, Pass Transistor Logic.8

The VTC is for pseudo-NMOS inverter with NMOS size of  $0.5 \mu\text{m}/0.25 \mu\text{m}$ . It demonstrates the effect of load transistor size on VTC.

From the curves, higher  $(W/L)_p$  gives higher  $V_{OL}$  and higher static power consumption (and vice versa).

**Exercise: Calculate  $V_{OL}$  using approx. eq. on p. 4 for case  $(W/L)_p = 4$ . Use transistor parameters on MOSFET transparency p. 22. Hint: Answer in text p. 266 is wrong!**

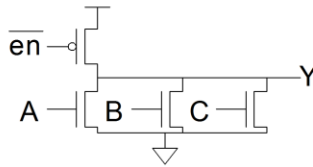
**Exercise: Repeat for case  $(W/L)_p = 2$ .**

**Exercise: Explain why answer is more accurate for 2<sup>nd</sup> case.**



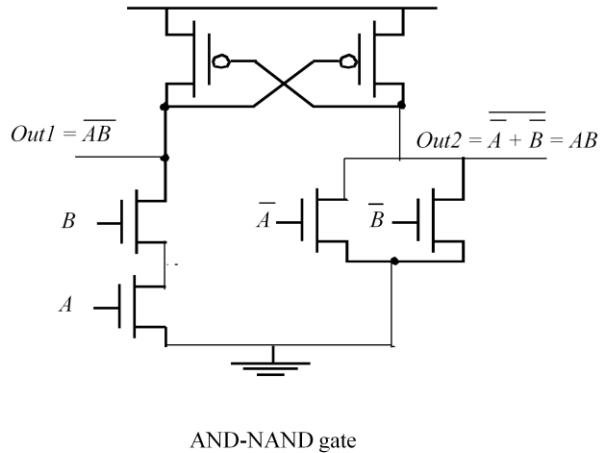
## Pseudo-nMOS Power

- ❑ Pseudo-nMOS draws power whenever output is 0
  - static power
    - $P = I_{DD}V_{DD}$
  - A few  $\mu\text{A}/\text{gate} \times 1\text{M}$  gates would be a problem
- ❑ Use pseudo-nMOS sparingly for wide NORs
- ❑ Turn off pMOS when not in use





## DCVSL Example



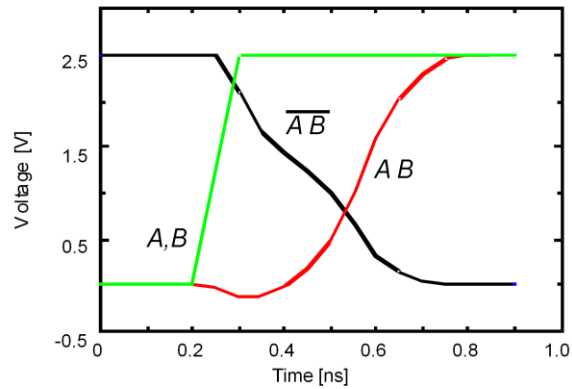
Ratioed, Pass Transistor Logic.11

If PDN1 is on, PDN2 is off, and vice versa.

Both outputs are at rail voltages (GND or  $V_{DD}$ ). Steady state power dissipation is eliminated.

The circuit is still ratioed. Why? Say  $A = B = 0$  V. Hence  $Out1$  should be  $V_{DD}$  and  $Out2 = GND$ . Thus left PMOS is on. When  $A = B = 1$ ,  $Out1$  should be LOW, which can be achieved by making sure the on resistance of PDN1 is low enough compared to on resistance of the left PMOS.

## DCVSL Transient Response (AND-NAND gate)



Ratioed, Pass Transistor Logic.12

Transistor dimensions used in the simulation

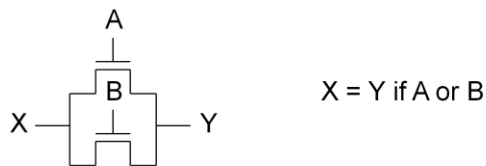
A and B transistors:  $1\ \mu\text{m}/0.25\ \mu\text{m}$

$\bar{A}$  and  $\bar{B}$  transistors:  $0.5\ \mu\text{m}/0.25\ \mu\text{m}$

PMOS transistors:  $1.5\ \mu\text{m}/0.25\ \mu\text{m}$

## NMOS Transistors in Series/Parallel

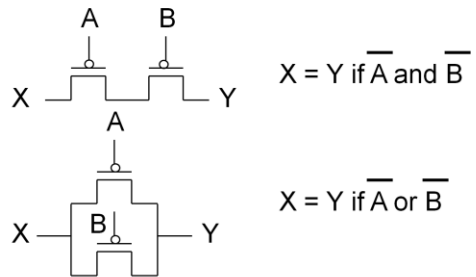
- Primary inputs drive both gate and source/drain terminals
- NMOS switch closes when the gate input is high



- Remember - NMOS transistors pass a **strong** 0 (output at 0 V) but a **weak** 1 (output at  $V_{DD} - V_{Tn}$ )

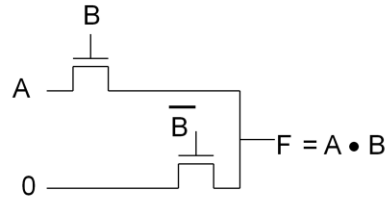
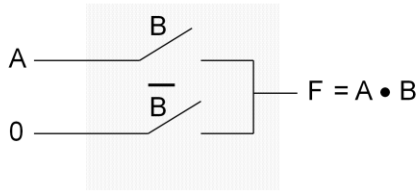
## PMOS Transistors in Series/Parallel

- PMOS switch closes when the gate input is low



- Remember - PMOS transistors pass a **strong** 1 but a **weak** 0

## Pass Transistor (PT) Logic



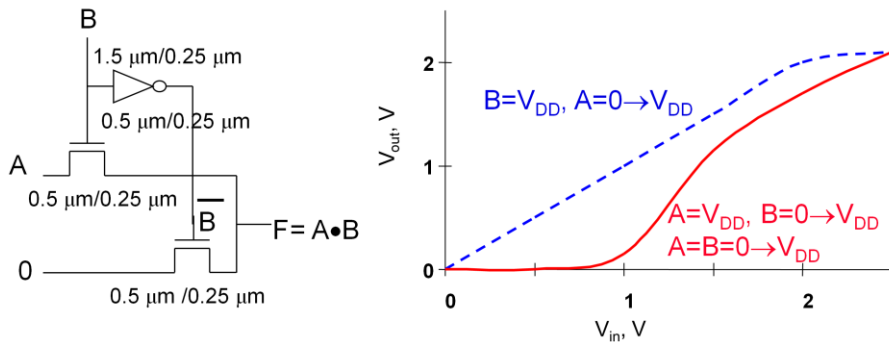
- ❑ Gate is static – a low-impedance path exists to both supply rails under all circumstances
- ❑ **N** transistors instead of **2N**
- ❑ No static power consumption
- ❑ Ratioless
- ❑ Bidirectional (versus unidirectional)

Ratioed, Pass Transistor Logic.15

This is pass transistor AND gate. How many transistors would it take to implement the same function in static comp. CMOS?

The switch driven by  $\overline{B}$  seems to be redundant. It is needed to ensure that a low impedance path exists to the supply rails under all circumstances. If the  $\overline{B}$  transistor is eliminated, what is the output when B is low?

## VTC of PT AND Gate



- Pure PT logic is not **regenerative** - the signal gradually degrades after passing through a number of PTs (can be fixed with static CMOS inverter insertion)

Ratioed, Pass Transistor Logic.16

VTC is data dependent.

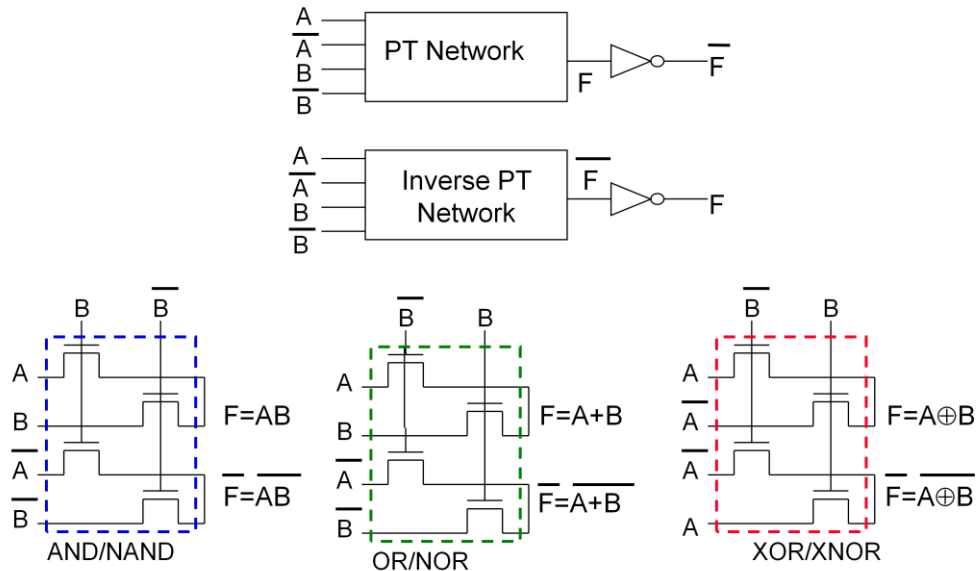
For dotted line – Top pass transistor on, bottom off, input A rises from  $0 \rightarrow V_{\text{DD}}$ . Initially,  $V_{\text{out}} = A$ . When  $V_{\text{out}} = V_{\text{DD}} - V_{\text{Th}}$  ( $\sim 2.1 \text{ V}$  in this example), output stops rising although A increases. **Exercise: Explain why.**

For case where  $A = V_{\text{DD}}$  and B rises from  $0 \rightarrow V_{\text{DD}}$ , bottom transistor stays on (hence  $V_{\text{out}}$  is almost  $0 \text{ V}$ ) until the inverter switches to zero (at  $\sim V_{\text{DD}}/2$ ).  $V_{\text{out}}$  only rises once the bottom pass transistor turns off.

Observe that a pure PT gate is not **REGENERATIVE**. A gradual signal degradation will be observed after passing through a number of subsequent gates. Output degradation can be remedied by occasional insertion of a CMOS inverter.



## Complementary PT Logic (CPL)



Ratioed, Pass Transistor Logic.17

How are the circuits built?

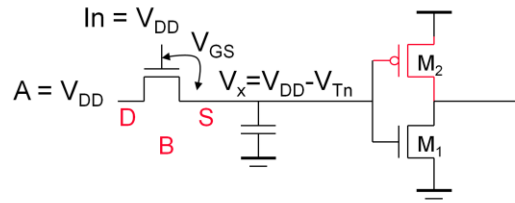
For NAND gate as an example,  $OUT = \overline{(AB)}$ . We can rewrite  $OUT = \overline{B} + \overline{A}$ . We further rewrite  $OUT = \overline{B}B + \overline{A}A$ . Hence transistor driven by  $\overline{B}$  is sourced by  $B$  and transistor driven by  $\overline{A}$  is sourced by  $A$ .

For OR gate,  $OUT = A + B$ . We can rewrite  $OUT = (\overline{B})A + B$ . We further rewrite  $OUT = (\overline{B})A + BB$ . Hence transistor driven by  $\overline{B}$  is sourced by  $A$  and transistor driven by  $B$  is sourced by  $B$ .

## CPL Properties

- ❑ CPL gates are **differential** circuits, hence complementary data inputs and outputs are always available
- ❑ Still static, since the output nodes are always tied to either  $V_{DD}$  or GND through a low resistance path
- ❑ Design is **modular**; all gates use the same topology, only the inputs are permuted
- ❑ Simple XOR makes it attractive for structures like **adders**
- ❑ Fast (assuming number of transistors in series is small)
- ❑ Additional routing overhead due to complementary signals

## NMOS Only PT Driving an Inverter

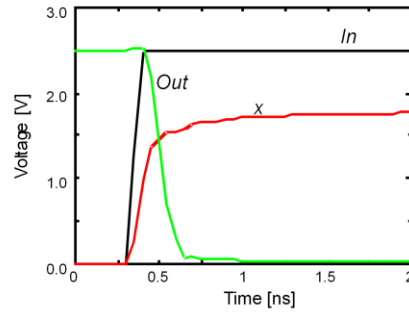
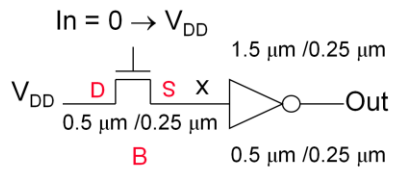


- $V_x$  does not pull up to  $V_{DD}$ , but  $V_{DD} - V_{Tn}$
- Threshold voltage drop causes static power consumption ( $M_2$  may be weakly conducting, since its gate is not at  $V_{DD}$ , allowing current to flow from  $V_{DD}$  to GND via  $M_2$  and  $M_1$ )
- $V_{Tn}$  of PT increases because **body effect** ( $V_{SB} \sim V_{DD}$  for case above)

Ratioed, Pass Transistor Logic.19

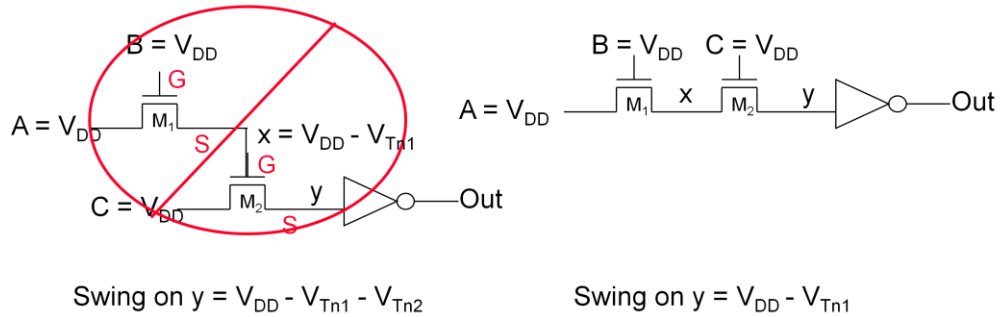
Body potential is at GND, hence  $V_{SB} = V_S$ .

## Voltage Swing of PT Driving an Inverter



- ❑ **Body effect** due to large  $V_{SB}$ .
- ❑ From simulation result,  $Out \sim 1.8 \text{ V}$ . Since  $Out = V_{DD} - V_{Tn}$ , we can deduce that  $V_{Tn} \sim 0.7 \text{ V}$  (note:  $V_{Tn0} = 0.43 \text{ V}$ ).

## Cascaded NMOS Only PTs



Swing on y =  $V_{DD} - V_{Tn1} - V_{Tn2}$

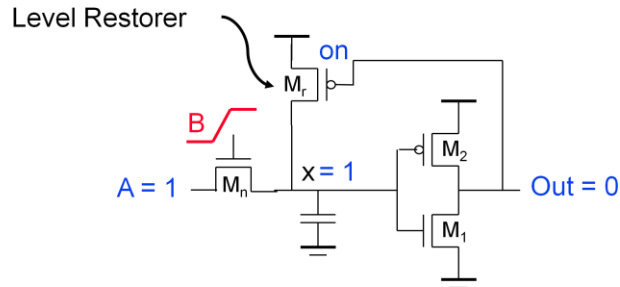
Swing on y =  $V_{DD} - V_{Tn1}$

- Pass transistor gates should **never** be cascaded as on the left
- Logic on the right suffers from static power dissipation (by inverter) and reduced noise margins

Ratioed, Pass Transistor Logic.21

For circuit on the right, what is  $V_y$  if  $V_C = V_{DD} - V_{Tn2}$ ?

## Solution 1: Level Restorer



- ❑ Full swing on x (due to Level Restorer) so no static power consumption by inverter
- ❑ For correct operation  $M_r$  must be sized correctly (**ratioed**)
- ❑ Restorer has speed and power impacts: increases the capacitance at x, slowing down the gate; increases  $t_r$  of Out (but decreases  $t_f$ )

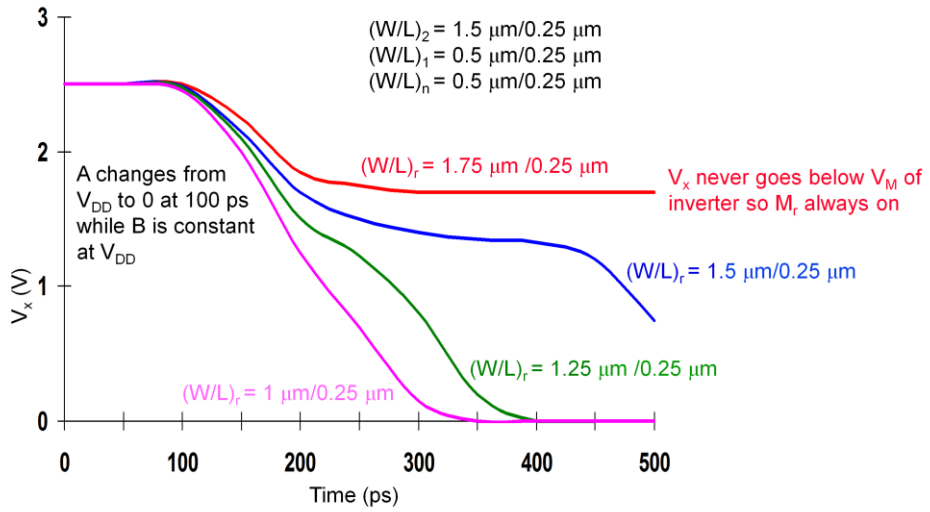
Ratioed, Pass Transistor Logic.22

Why ratioed?

When node x is 1 but logically should change to 0 (for e.g. when A changes to 0, while B remains 1), the pull-down network through  $M_n$  must be stronger than the pull-up network of  $M_r$  in order to switch node x to 0. If  $R_r$  is too small (i.e.  $W_r$  is too large), it is impossible to bring the voltage at node x below the switching threshold of the inverter.

Without  $M_r$ , x can be discharged easily. Out rise time is fast (assuming Out is initially low). With  $M_r$  present, it is on if Out is initially low. When x is to be discharged,  $M_n$  has to fight with the restorer. Hence x is discharged more slowly, which increases rise time of Out.

## Transient Level Restorer Circuit Response

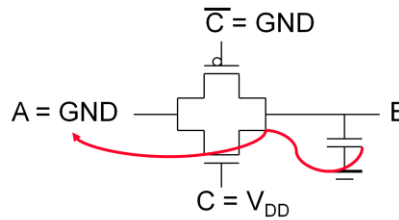
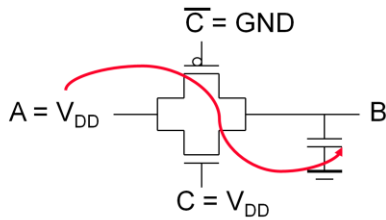
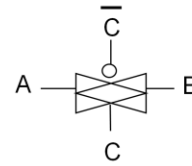
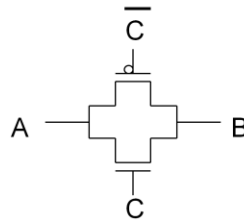


Ratioed, Pass Transistor Logic.23

Sizing of  $M_r$  is critical for DC functionality, not just performance!

## Solution 2: Transmission Gates (TGs)

- Most widely used solution



- Full swing** *bidirectional* switch controlled by the gate signal C.  
A = B if C = 1. If C = 0, both transistors are off.

Ratioed, Pass Transistor Logic.24

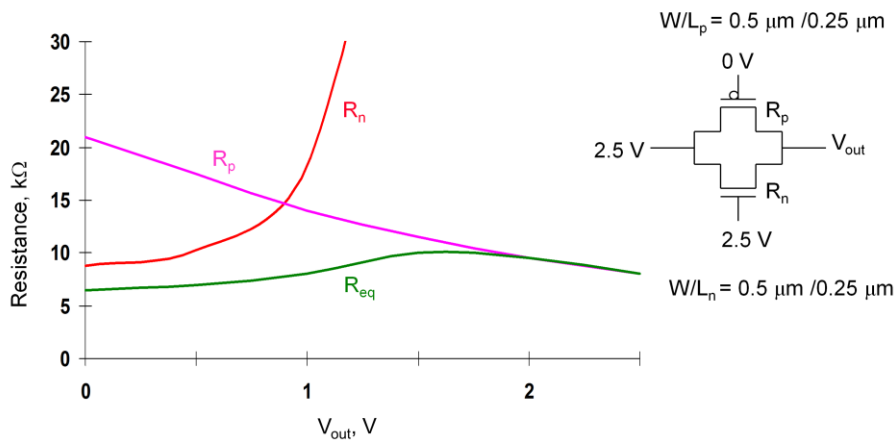
Use the NMOS to ensure both input and output terminals exactly equal to 0.  
Use the PMOS to ensure both terminals exactly at  $V_{DD}$ .

Use minimum size for both transistors. Increasing W/L has no net impact on switching delay (reduces resistance but increases diffusion capacitance).

Ratioless logic.



## Resistance of TG



Ratioed, Pass Transistor Logic.25

Transmission gate is not an ideal switch – has series resistance.

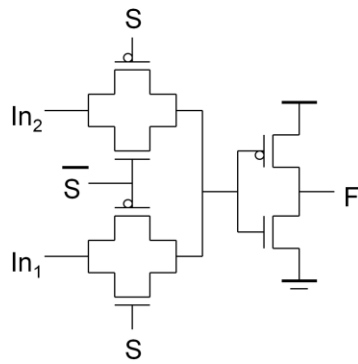
Effective resistance modeled as parallel connection of  $R_p$  and  $R_n$  ( $R_p = (V_{DD} - V_{out})/I_p$ ).

For  $R_n$ , at low values of  $V_{out}$ , it is in saturation, hence has low resistance. As  $V_{out}$  increases, resistance increases to infinity (as device shuts off).

For  $R_p$ , at low values of  $V_{out}$ , it is in saturation. As  $V_{out}$  approaches  $V_{DD}$ , it operates in linear mode.

$R_{eq} = R_p \parallel R_n$  is relatively constant (about 8 kohms in this case).

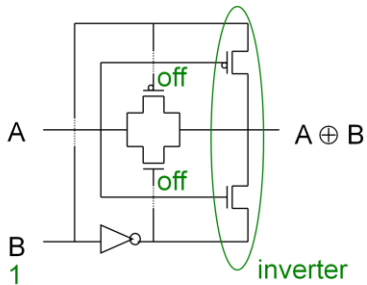
## TG Multiplexer



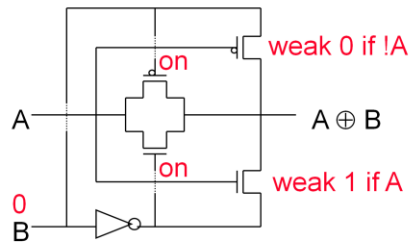
$$F = \overline{(In_1 \cdot S + In_2 \cdot \bar{S})}$$

Complementary CMOS circuit has 8 transistors.

## Transmission Gate XOR



output =  $\neg A$  when  $B = 1$



When  $B = 0$ , output = A. TG guarantees perfect output whatever A is.

6 transistor implementation of XOR (versus 10 for complementary CMOS).

Output always has a connection to either VDD or GND.

## Pass Transistor Summary

- Researchers investigated pass transistor logic for general purpose applications in the 1990's
  - benefits over static CMOS were small or negative
  - no longer generally used
- However, pass transistors still have niche in special circuits such as memories
  - they offer small size
  - threshold drops can be managed